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Kind regards,

Team Nexperia

PDTA143E series

PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

Rev. 8 — 8 December 2011

Product data sheet

1. Product profile

1.1 General description

PNP Resistor-Equipped Transistor (RET) family in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package			NPN	Package	
	NXP	JEITA	JEDEC	complement	configuration	
PDTA143EE	SOT416	SC-75	-	PDTC143EE	ultra small	
PDTA143EM	SOT883	SC-101	-	PDTC143EM	leadless ultra small	
PDTA143ET	SOT23	-	TO-236AB	PDTC143ET	small	
PDTA143EU	SOT323	SC-70	-	PDTC143EU	very small	

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Digital applications in automotive and industrial segments
- Control of IC inputs

- Cost-saving alternative for BC847/857 series in digital applications
- Switching loads

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-50	V
Io	output current		-	-	-100	mA
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



2. Pinning information

Table 3. **Pinning** Simplified outline **Graphic symbol** Pin **Description** SOT23; SOT323; SOT416 1 input (base) 3 GND (emitter) 2 3 output (collector) 2 006aaa144 sym003 **SOT883** 1 input (base) 2 GND (emitter) output (collector) Transparent

3. Ordering information

Table 4. Ordering information

Type number	Package	Package						
	Name	Description	Version					
PDTA143EE	SC-75	plastic surface-mounted package; 3 leads	SOT416					
PDTA143EM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883					
PDTA143ET	-	plastic surface-mounted package; 3 leads	SOT23					
PDTA143EU	SC-70	plastic surface-mounted package; 3 leads	SOT323					

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PDTA143EE	01
PDTA143EM	DL
PDTA143ET	*01
PDTA143EU	*01

[1] * = placeholder for manufacturing site code

sym003

5. Limiting values

Table 6. Limiting values

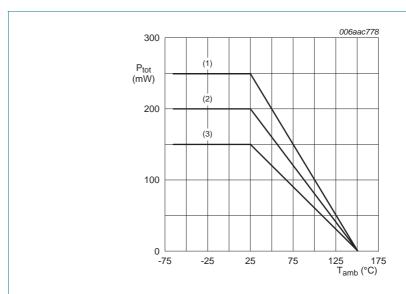
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-50	V
V_{EBO}	emitter-base voltage	open collector	-	-10	V
V_{I}	input voltage				
	positive		-	+10	V
	negative		-	-30	V
Io	output current		-	-100	mA
I _{CM}	peak collector current	$single \ pulse; \\ t_p \leq 1 \ ms$	-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PDTA143EE (SOT416)		[1][2]	150	mW
	PDTA143EM (SOT883)		[2][3]	250	mW
	PDTA143ET (SOT23)		<u>[1]</u> _	250	mW
	PDTA143EU (SOT323)		<u>[1]</u> _	200	mW
T _j	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

^[3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



- (1) SOT23; FR4 PCB, standard footprint SOT883; FR4 PCB with 70 μm copper strip line, standard footprint
- (2) SOT323; FR4 PCB, standard footprint
- (3) SOT416; FR4 PCB, standard footprint

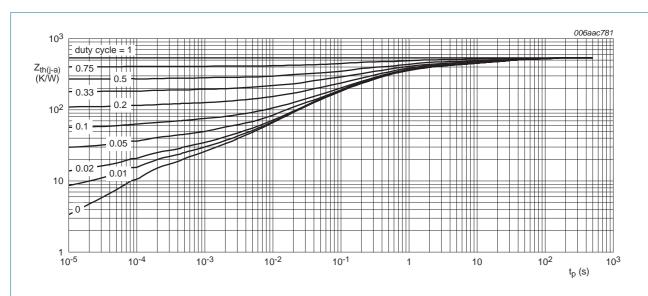
Fig 1. Power derating curves

6. Thermal characteristics

Table 7. Thermal characteristics

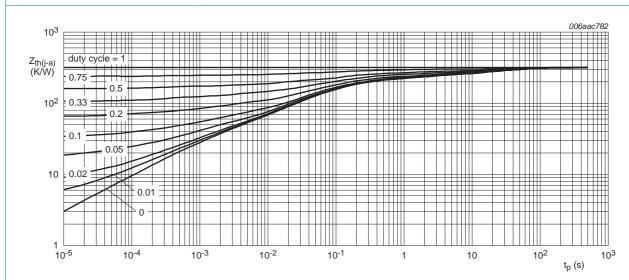
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PDTA143EE (SOT416)		[1][2]	-	830	K/W
	PDTA143EM (SOT883)		[2][3]	-	500	K/W
	PDTA143ET (SOT23)		[1] -	-	500	K/W
	PDTA143EU (SOT323)		<u>[1]</u> _	-	625	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



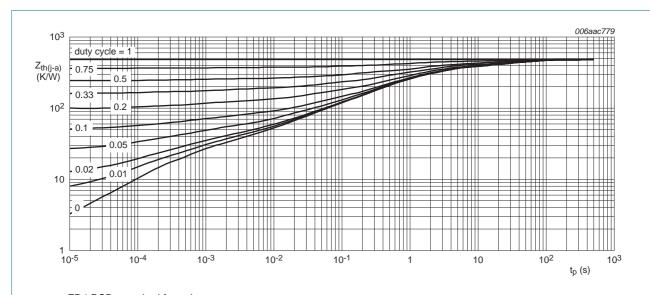
FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA143EE (SOT416); typical values



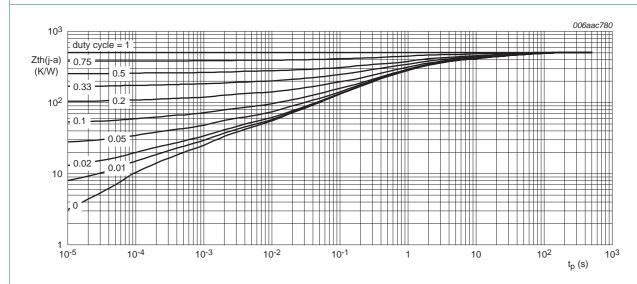
FR4 PCB, 70 µm copper strip line

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA143EM (SOT883); typical values



FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA143ET (SOT23); typical values



FR4 PCB, standard footprint

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA143EU (SOT323); typical values

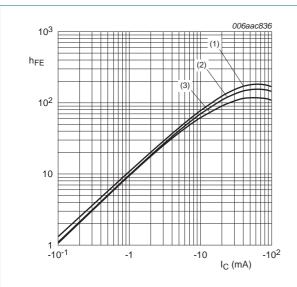
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}$	-	-	-1	μΑ
cut-off current	cut-off current	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	- 5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-900	μА
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}$	30	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	-	-	-150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	-	-1.1	-0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = -0.3 \text{ V};$ $I_{C} = -20 \text{ mA}$	-2.5	-1.9	-	V
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		8.0	1	1.2	
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = I_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}; $ [1] $f = 100 \text{ MHz}$	-	180	-	MHz

^[1] Characteristics of built-in transistor



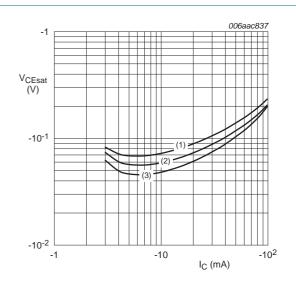
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig 6. DC current gain as a function of collector current; typical values



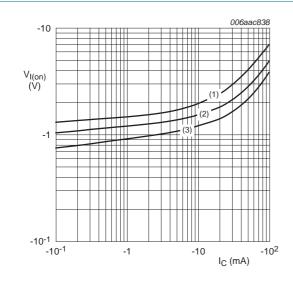
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



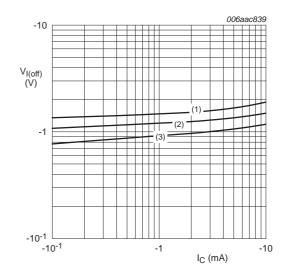
$$V_{CE} = -0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 8. On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 9. Off-state input voltage as a function of collector current; typical values

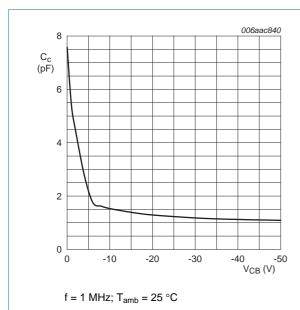


Fig 10. Collector capacitance as a function of collector-base voltage; typical values

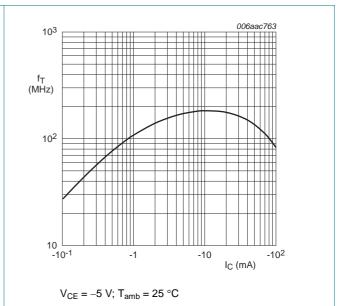


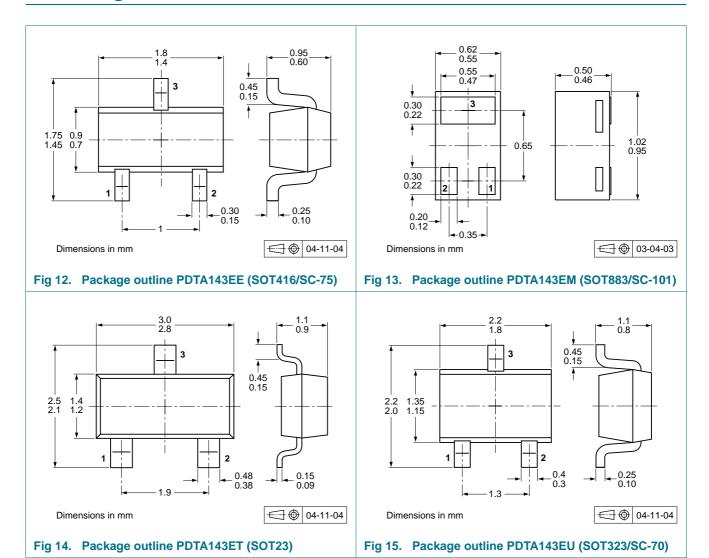
Fig 11. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	Packing quantity	
			3000	5000	10000
PDTA143EE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135
PDTA143EM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-315
PDTA143ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235
PDTA143EU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135

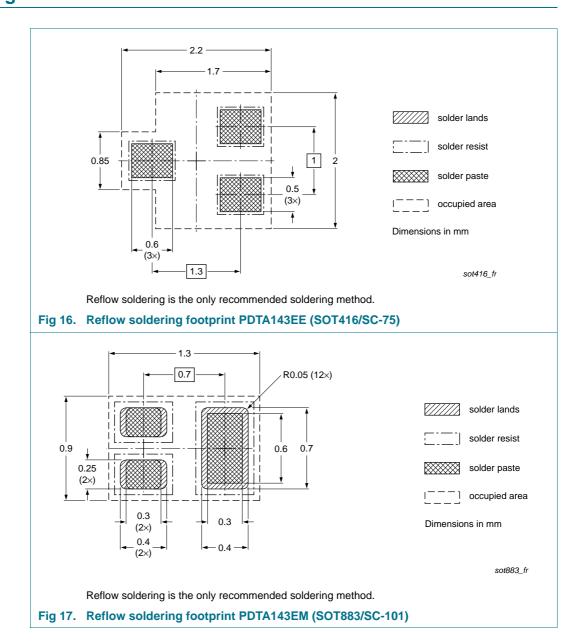
[1] For further information and the availability of packing methods, see Section 14.

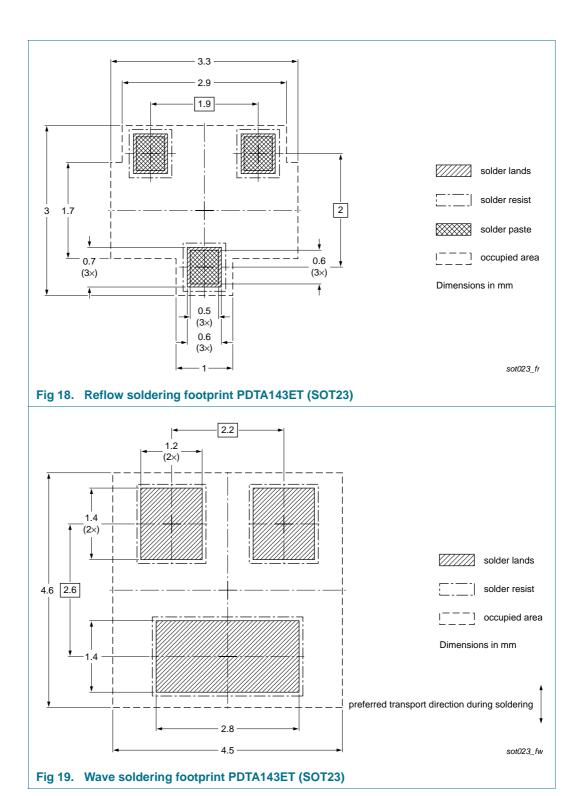
PDTA143E_SER

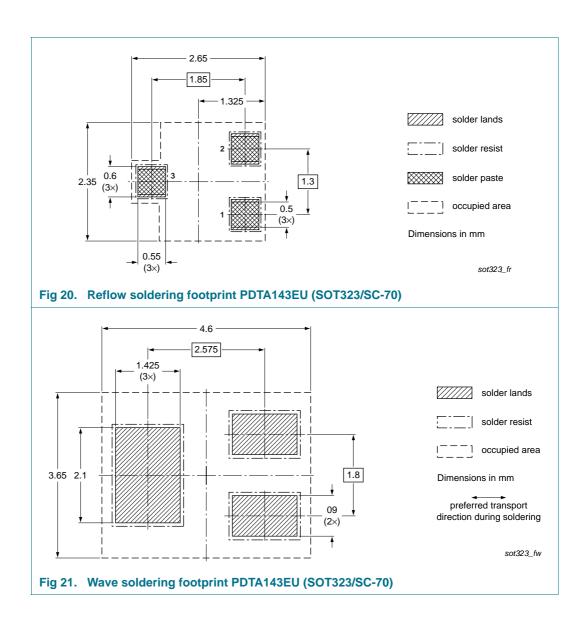
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11. Soldering







12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PDTA143E_SER v.8	20111208	Product data sheet	-	PDTA143E_SERIES v.7		
Modifications:		f this document has been r NXP Semiconductors.	edesigned to comply w	ith the new identity		
	 Legal texts h 	ave been adapted to the ne	ew company name whe	re appropriate.		
	 Type number 	rs PDTA143EEF, PDTA143	EK and PDTA143ES re	emoved.		
	 Section 1 "Pr 	roduct profile": updated				
	 Section 3 "O 	rdering information": added				
	 Section 4 "M 	arking": updated				
	• Figure 1 to 11: added					
	Section 6 "Thermal characteristics": updated					
	 <u>Table 8 "Characteristics"</u>: V_{i(on)} redefined to V_{I(on)} on-state input voltage, V_{i(off)} redefined to V_{I(off)} off-state input voltage, I_{CEO} updated, f_T added 					
	Section 8 "Test information": added					
	Section 9 "Package outline": superseded by minimized package outline drawings					
	 Section 10 "F 	Packing information": added	t			
	Section 11 "S	Soldering": added				
	 Section 13 "L 	<u>egal information"</u> : updated				
PDTA143E_SERIES v.7	20040804	Product data sheet	-	PDTA143E_SERIES v.6		
PDTA143E_SERIES v.6	20030908	Product specification	-	PDTA143E_SERIES v.5		
PDTA143E_SERIES v.5	20030411	Product specification	-	-		

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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PDTA143E_SER

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PDTA143E series

PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

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PDTA143E series

PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

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